Abstracts

Output Conductance Frequency Dispersion and Low-Frequency Noise in HEMT's and MESFET's (Short Papers)

J.A. Reynoso-Hernandez and J. Graffeuil. "Output Conductance Frequency Dispersion and Low-Frequency Noise in HEMT's and MESFET's (Short Papers)." 1989 Transactions on Microwave Theory and Techniques 37.9 (Sep. 1989 [T-MTT] (Special Issue on FET Structures Modeling and Circuit Applications)): 1478-1481.

In this paper it is reported that the large low-frequency noise observed in MESFET's and HEMT's in the saturation regime usually scales with the device output conductance frequency dispersion (in MESFET's) or with the parallel conduction through the GaAlAs (in HEMT's).

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